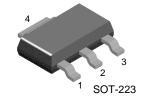


# **BSP52**

# **NPN Darlington Transistor**

- This device is designed for applications requiring extremly high current gain at collector currents to 500mA.
- Sourced from process 03.



1. Base 2. Collector 3. Emitter

# **Absolute Maximum Ratings\*** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	80	V
$V_{CBO}$	Collector-Base Voltage	90	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

  1) These ratings are based on a maximum junction temperature of 150°C.

  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Electrical Characteristics T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	Off Characteristics					
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	90			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5			V
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = 80V, V_{BE} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0V, I_{C} = 0$			10	μΑ
On Characteristics						
h <sub>FE</sub>	DC Current Gain	$I_C = 150 \text{mA}, V_{CE} = 10 \text{V}$	1000			
		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$	2000			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$			1.3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$			1.9	V

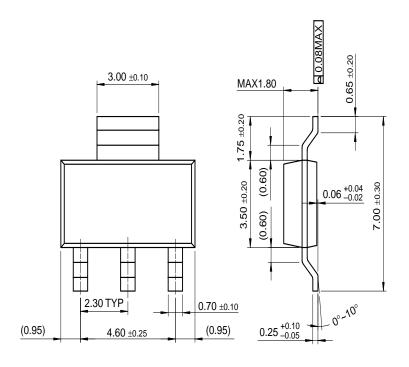
# Thermal Characteristics $T_A=25$ °C unless otherwise noted

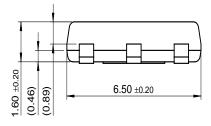
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	1000	mW
	Derate above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

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# **Package Demensions**

# **SOT-223**





Dimensions in Millimeters

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DOME™	HiSeC™	Power247™	SuperSOT™-6	
EcoSPARK™	I <sup>2</sup> C™	PowerTrench <sup>®</sup>	SuperSOT™-8	
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EnSigna™	LittleFET™	QS™	TinyLogic™	
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FACT Quiet series™	MicroPak™	Quiet Series™	UHC™	
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